

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## AON7430-MS

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Product specification

## Description

The AON7430-MS uses advanced trench technology to provide excellent RDS(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

## Features

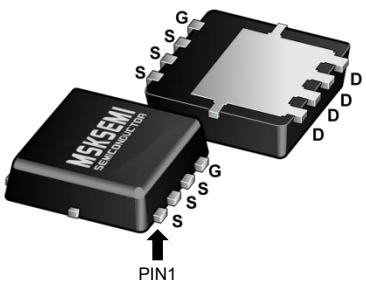
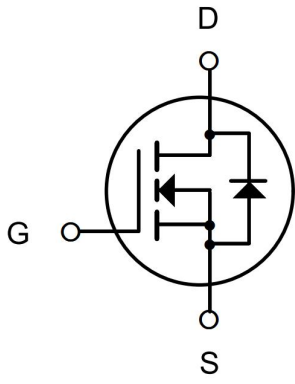

VDS = 30V ID =30 A

RDS(ON) < 13mΩ @ VGS=10V

## Application

- Battery protection
- Load switch
- Uninterruptible power supply

## Reference News

PACKAGE OUTLINE	N-Channel MOSFET	Marking
 <p>DFN3X3-8L</p>		

## Absolute Maximum Ratings (TC=25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	30	V
VGS	Gate-Source Voltage	±20	V
Id@Tc=25°C	Continuous Drain Current, VGS @ 10V <sup>1</sup>	30	A
Id@Tc=100°C	Continuous Drain Current, VGS @ 10V <sup>1</sup>	18	A
IDM	Pulsed Drain Current <sup>2</sup>	55	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	22.1	mJ
IAS	Avalanche Current	21	A
Pd@Tc=25°C	Total Power Dissipation <sup>4</sup>	20	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
RθJA	Thermal Resistance Junction-ambient <sup>1</sup>	75	°C/ W
RθJC	Thermal Resistance Junction-Case <sup>1</sup>	6	°C/ W

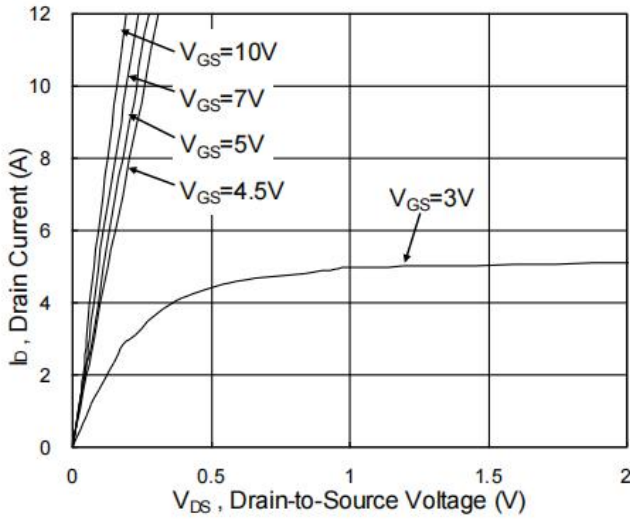
**Electrical Characteristics** (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =1mA	---	0.022	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V , I <sub>D</sub> =10A	---	8	13	mΩ
		V <sub>GS</sub> =4.5V , I <sub>D</sub> =5A	---	12	20	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	---	2.5	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	-5.1	---	Mv/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ± 20V , V <sub>DS</sub> =0V	---	---	± 100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =5V , I <sub>D</sub> =1A	---	4.5	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz	---	2.5	---	Ω
Q <sub>g</sub>	Total Gate Charge (4.5V)	V <sub>DS</sub> =20V , V <sub>GS</sub> =4.5V , I <sub>D</sub> =10A	---	7.2	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	1.4	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	2.2	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =12V , V <sub>GS</sub> =10V , R <sub>G</sub> =3.3 I <sub>D</sub> =5A	---	4.1	---	ns
T <sub>r</sub>	Rise Time		---	9.8	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	15.5	---	
T <sub>f</sub>	Fall Time		---	6.0	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V , V <sub>GS</sub> =0V , f=1MHz	---	572	---	pF
C <sub>oss</sub>	Output Capacitance		---	81	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	65	---	
I <sub>s</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	28	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	55	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =1A , T <sub>J</sub> =25°C	---	---	1.2	V

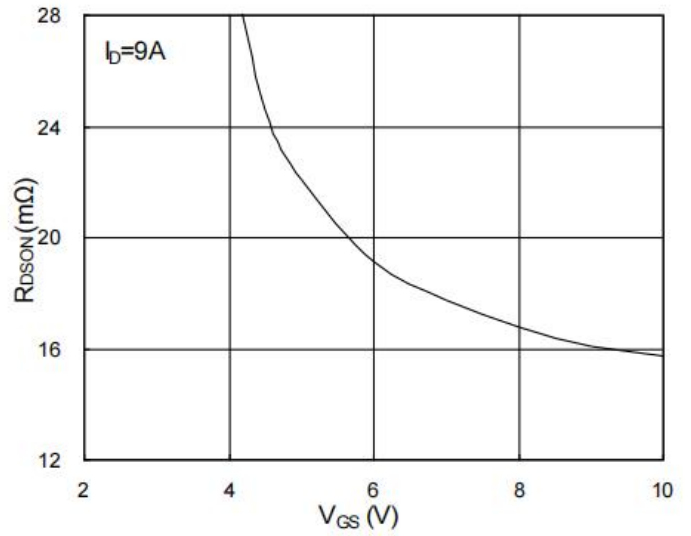
**Note :**

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup>FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%
- 3.The EAS data shows Max. rating . The test condition is V<sub>DD</sub>=25V,V<sub>GS</sub>=10V,L=0.1mH,I<sub>AS</sub>=21A
- 4 .The power dissipation is limited by 150°C junction temperature 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub> , in real applications , should be limited by total power dissipation.

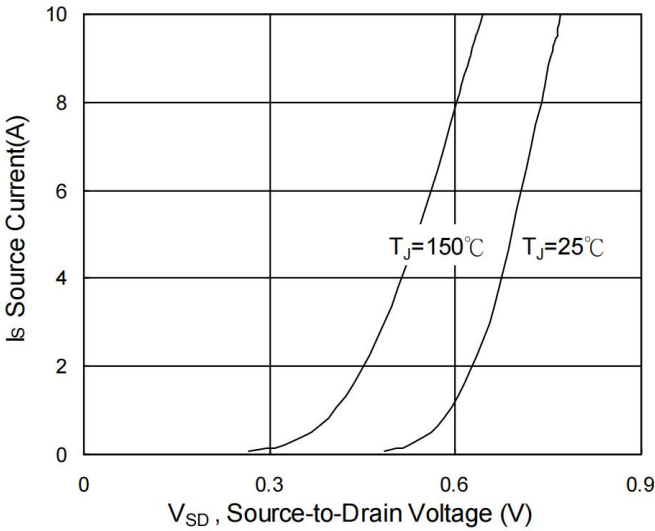
**Typical Characteristics**



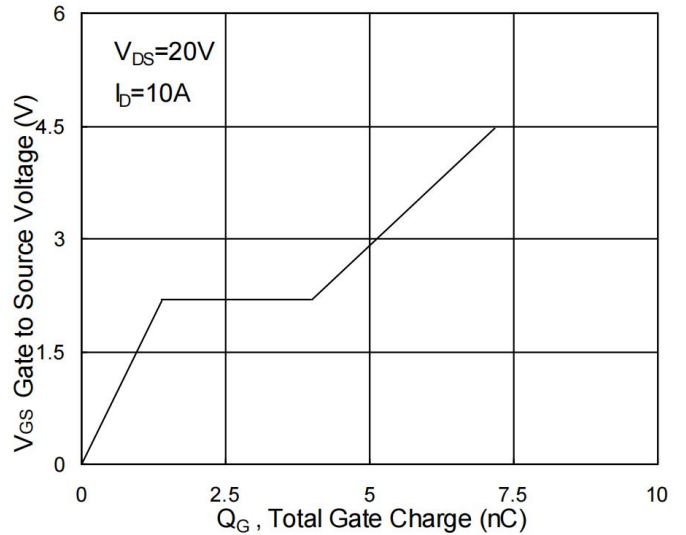
**Fig.1 Typical Output Characteristics**



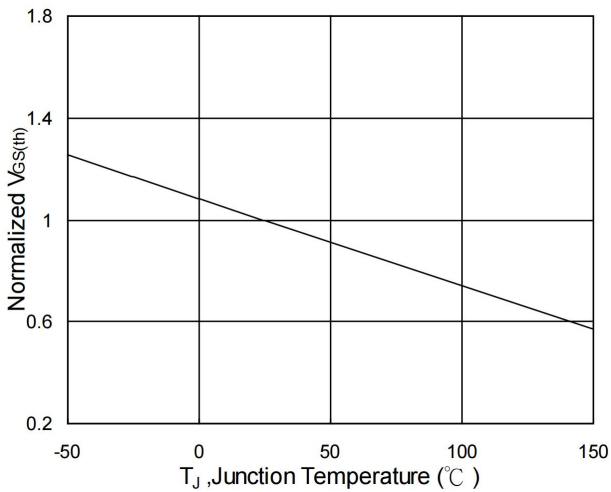
**Fig.2 On-Resistance vs. G-S Voltage**



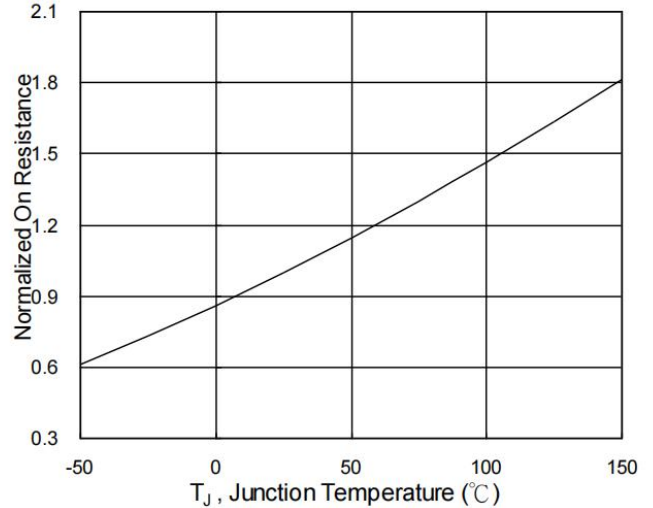
**Fig.3 Forward Characteristics of Reverse**



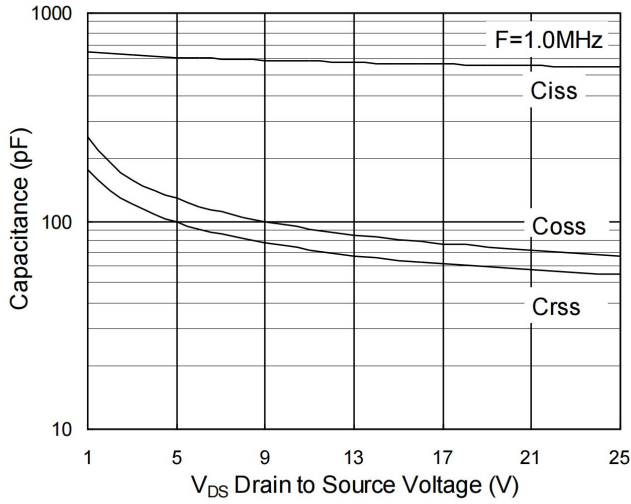
**Fig.4 Gate-Charge Characteristics**



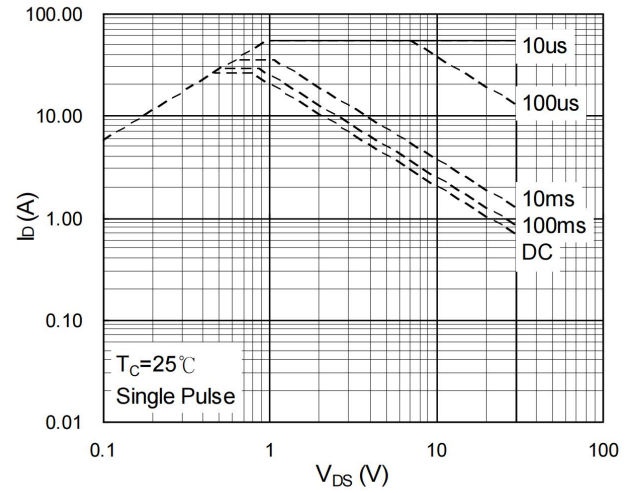
**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



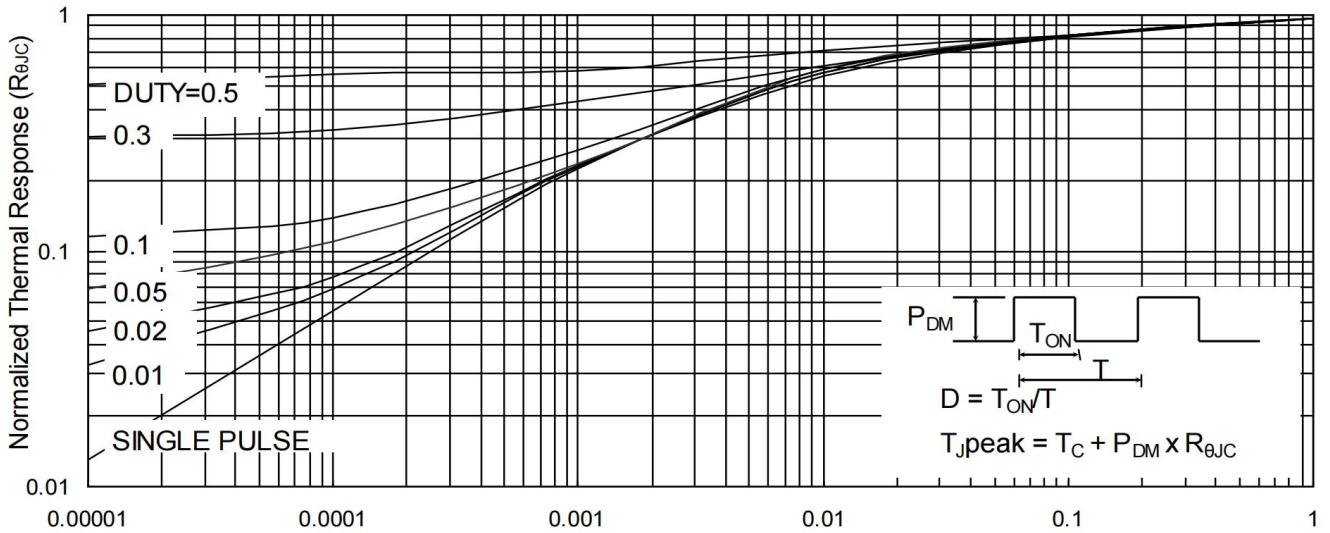
**Fig.6 Normalized  $R_{DS(on)}$  vs.  $T_J$**



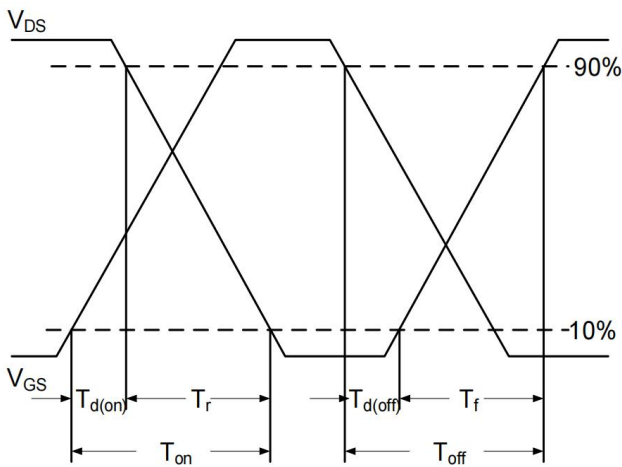
**Fig.7 Capacitance**



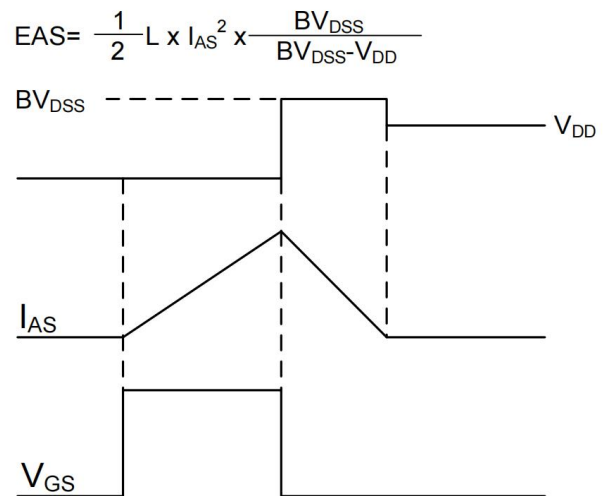
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**



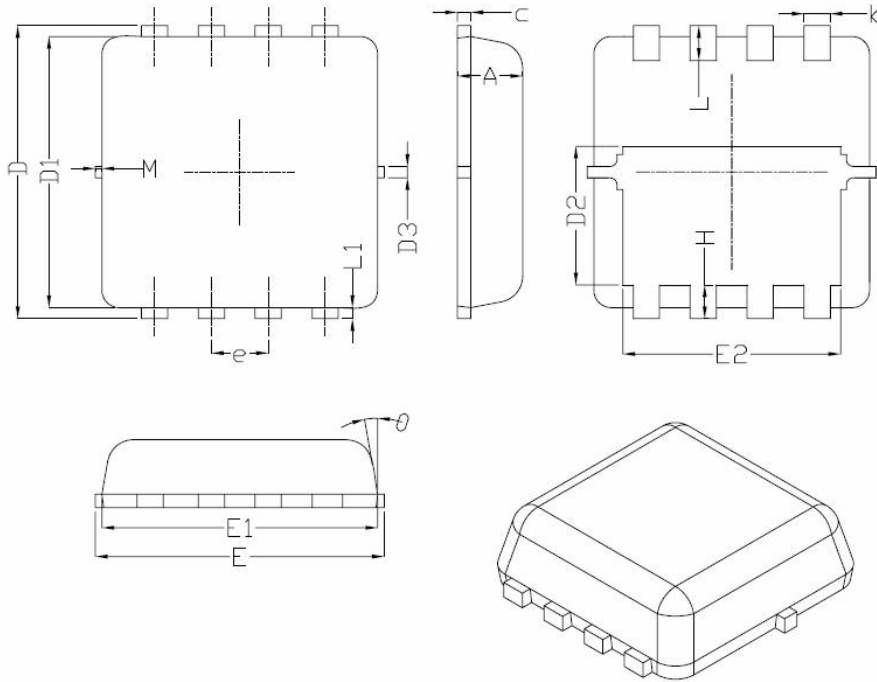
**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

**DFN3X3-8L Package Information**



Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ		10°	12°

**REEL SPECIFICATION**

P/N	PKG	QTY
AON7430-MS	DFN3X3-8L	5000

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